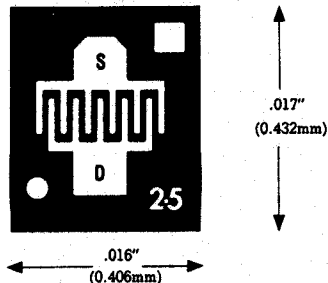


CHIP NUMBER

FN3.6



Die Size: .16 x .17 (mils)
0.406 x 0.432(mm)
3 x 3 (mils)
Pad Size: 0.076 x 0.076(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum
Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

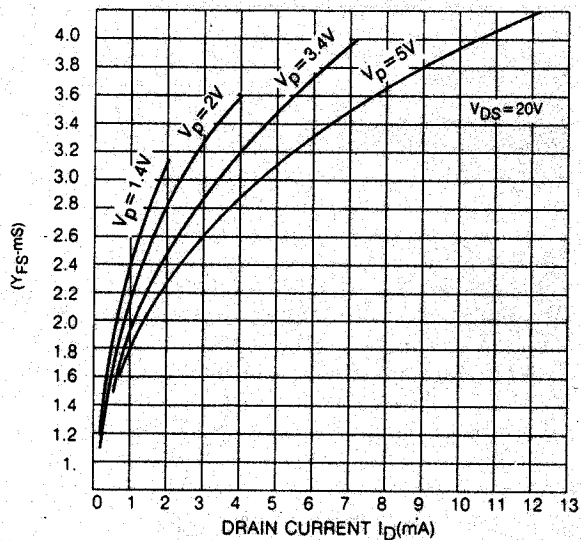
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-30	-50	-70	V	$V_{DS} = 0, I_G = 1\mu A$
I_{DSS}	0.5	8.0	20	mA	$V_{DS} = 15V, V_{GS} = 0$
g_{fs}	1.5	4.0	6.0	mmho	$V_{DS} = 15V, V_{GS} = 0$
I_{GSS}		25	100	pA	$V_{GS} = -30V, V_{DS} = 0$
r_{DS}	150	200	600	Ω	$V_{DS} = 100mV, V_{GS} = 0$
$V_{GS(off)}$	-1.0	-3.0	8.0	V	$V_{DS} = 15V, I_D = 1nA$
C_{rss}	1.2	2.0	3.0	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$
C_{iss}		4.5	6.0	pF	$V_{DS} = 15V, V_{GS} = 0, f = 1MHz$

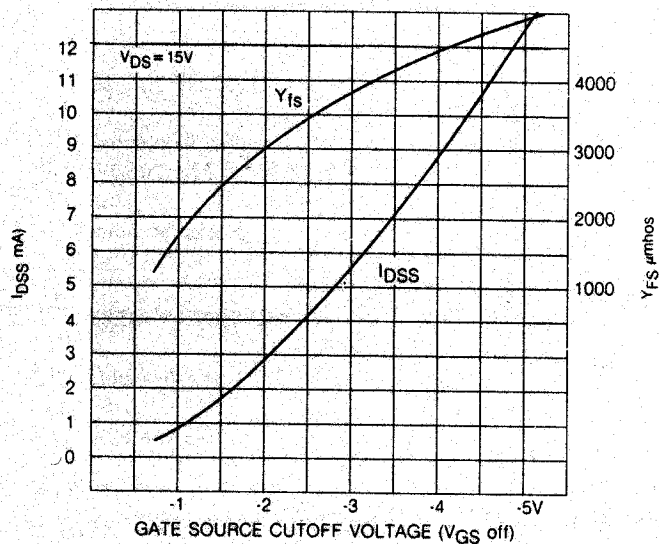
TYPICAL DEVICE TYPES: 2N3821 - 2N3824, 2N3921 - 2N3922, 2N5545 - 2N5547

CHIP TYPE FN3.6

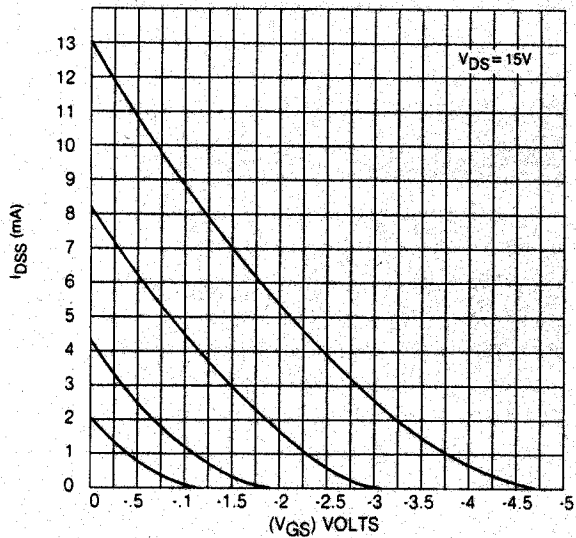
FORWARD TRANSADMITTANCE
VS. OPERATING DRAIN CURRENT



FORWARD TRANSADMITTANCE VS



TRANSFER CHARACTERISTICS



OUTPUT CHARACTERISTICS

